



3DK9



NPN Silicon High Frequency M-Power Switch Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications								Test Condition
			A	B	C	D	E	F	G	H	
Total Dissipation	P_{tot}	mW	700								$T_a=25^\circ\text{C}$
Max. Collector Current	I_{CM}	mA	800								
Junction Temperature	T_{jm}	$^\circ\text{C}$	175								
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175								
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	25	50	75	100	25	50	75	100	$I_C=0.1\text{mA}$
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	20	35	60	80	20	35	60	80	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	5								$I_E=0.1\text{mA}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5								$I_C=300\text{mA}$ $I_B=30\text{mA}$
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.2								
C-E Leakage Current	I_{CEO}	μA	5				3				$V_{CE}=15\text{V}$
DC Current Gain	h_{FE}		Orange: 25~40, Yellow: 40~55, Green: 55~80 Blue: 80~120, Purple: 120~180								$V_{CE}=5\text{V}, I_C=300\text{mA}$
Transition frequency	f_T	MHz	120								$V_{CE}=10\text{V}, I_C=60\text{mA}$ $f=100\text{MHz}$
Turn-on Time	t_{on}	ns	100				80				$I_C=300\text{mA}$ $I_{B1}=I_{B2}=30\text{mA}$
Storage Time	t_s	ns	180				170				
Fall Time	t_f	ns	50								

Outline and Dimensions: